

Easy and accurate empirical transistor model parameter estimation from vectorial large-signal measurements

D. Schreurs, J. Verspecht, S. Vandenberghe, G. Carchon, K. van der Zanden and B. Nauwelaers. "Easy and accurate empirical transistor model parameter estimation from vectorial large-signal measurements." 1999 MTT-S International Microwave Symposium Digest 99.2 (1999 Vol. II [MWSYM]): 753-756 vol.2.

The standard empirical nonlinear model parameter estimation is often cumbersome as several measurement systems are involved. We show that the model generation complexity can be reduced tremendously by only using full two-port vectorial large-signal measurements. Furthermore, realistic operating conditions can easily be included in the optimisation procedure, as we illustrate on GaAs PHEMTs.

 [Return to main document.](#)